



Description

The IRLR7843TRPBF uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



TO252-2L

General Features

$V_{DS} = 30V$ $I_D = 120A$

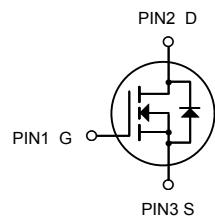
$R_{DS(ON)} < 3.8m\Omega$ @ $V_{GS}=10V$

Application

Battery protection

Load switch

Uninterruptible power supply



N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
IRLR7843TRPBF	TO252-2L	120N03 XXXX YYYY	2500

Absolute Maximum Ratings ($T_c=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_c=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	120	A
$I_D @ T_c=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	75	A
I_{DM}	Pulsed Drain Current ²	384	A
EAS	Single Pulse Avalanche Energy ³	196	mJ
I_{AS}	Avalanche Current	53.8	A
$P_D @ T_c=25^\circ C$	Total Power Dissipation ⁴	62.5	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	62	°C/W



Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$\text{V}_{\text{GS}}=0\text{V}, \text{I}_{\text{DS}}=250\mu\text{A}$	30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$\text{V}_{\text{DS}}=24\text{V}, \text{V}_{\text{GS}}=0\text{V}$	-	-	1	μA
		$\text{T}_J=85^\circ\text{C}$	-	-	30	
$\text{V}_{\text{GS(th)}}$	Gate Threshold Voltage	$\text{V}_{\text{DS}}=\text{V}_{\text{GS}}, \text{I}_{\text{DS}}=250\mu\text{A}$	1.4	1.7	2.5	V
I_{GSS}	Gate Leakage Current	$\text{V}_{\text{GS}}=\pm 20\text{V}, \text{V}_{\text{DS}}=0\text{V}$	-	-	± 100	nA
$\text{R}_{\text{DS(ON)}}^{\text{d}}$	Drain-Source On-state Resistance	$\text{V}_{\text{GS}}=10\text{V}, \text{I}_{\text{DS}}=20\text{A}$	-	3	3.8	$\text{m}\Omega$
		$\text{T}_J=125^\circ\text{C}$	-	4.4	-	
		$\text{V}_{\text{GS}}=4.5\text{V}, \text{I}_{\text{DS}}=15\text{A}$	-	4.0	5.5	
Gfs	Forward Transconductance	$\text{V}_{\text{DS}}=5\text{V}, \text{I}_{\text{DS}}=10\text{A}$	-	24.6	-	S
Diode Characteristics						
$\text{V}_{\text{SD}}^{\text{d}}$	Diode Forward Voltage	$\text{I}_{\text{SD}}=20\text{A}, \text{V}_{\text{GS}}=0\text{V}$	-	0.8	1.1	V
t_{rr}	Reverse Recovery Time	$\text{I}_{\text{DS}}=20\text{A}, \frac{d\text{I}_{\text{SD}}}{dt}=100\text{A}/\mu\text{s}$	-	35.6	-	ns
t_{a}	Charge Time		-	19.3	-	
t_{b}	Discharge Time		-	16.3	-	
Q_{rr}	Reverse Recovery Charge		-	26	-	nC
Dynamic Characteristics ^e						
R_{G}	Gate Resistance	$\text{V}_{\text{GS}}=0\text{V}, \text{V}_{\text{DS}}=0\text{V}, \text{F}=1\text{MHz}$	-	1	2	Ω
C_{iss}	Input Capacitance	$\text{V}_{\text{GS}}=0\text{V}, \text{V}_{\text{DS}}=15\text{V}, \text{Frequency}=1.0\text{MHz}$	-	2485	2971	pF
C_{oss}	Output Capacitance		-	850	-	
C_{rss}	Reverse Transfer Capacitance		-	85	-	
$\text{t}_{\text{d(ON)}}$	Turn-on Delay Time	$\text{V}_{\text{DD}}=15\text{V}, \text{R}_{\text{L}}=15\Omega, \text{I}_{\text{DS}}=1\text{A}, \text{V}_{\text{GEN}}=10\text{V}, \text{R}_{\text{G}}=6\Omega$	-	12.4	23	ns
t_{r}	Turn-on Rise Time		-	9.5	18	
$\text{t}_{\text{d(OFF)}}$	Turn-off Delay Time		-	27.2	49	
t_{f}	Turn-off Fall Time		-	35.2	64	
Gate Charge Characteristics ^e						
Q_{g}	Total Gate Charge	$\text{V}_{\text{DS}}=15\text{V}, \text{V}_{\text{GS}}=10\text{V}, \text{I}_{\text{DS}}=20\text{A}$	-	20.6	28.8	nC
Q_{g}	Total Gate Charge	$\text{V}_{\text{DS}}=15\text{V}, \text{V}_{\text{GS}}=4.5\text{V}, \text{I}_{\text{DS}}=20\text{A}$	-	9.8	-	
Q_{gth}	Threshold Gate Charge		-	1.8	-	
Q_{gs}	Gate-Source Charge		-	3.8	-	
Q_{gd}	Gate-Drain Charge		-	3.7	-	

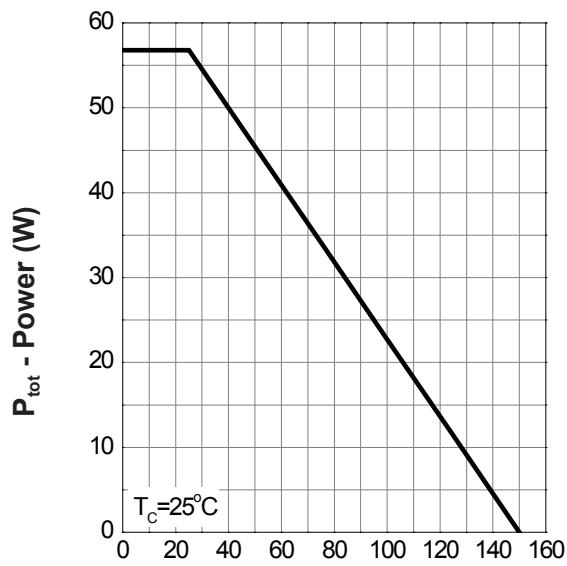
Note d : Pulse test ; pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.

Note e : Guaranteed by design, not subject to production testing.

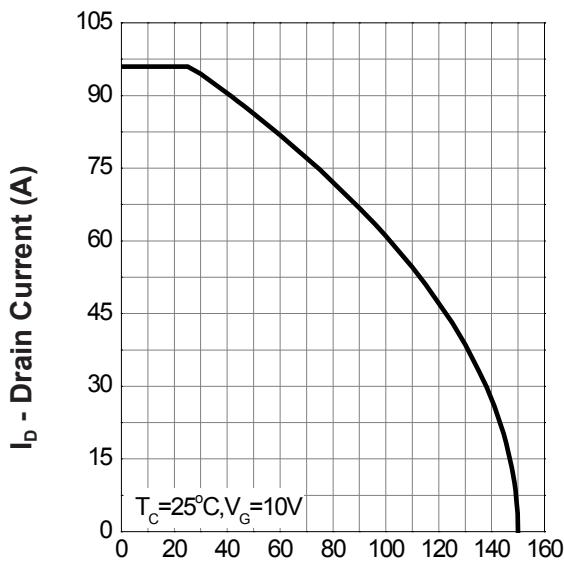


Typical Operating Characteristics

Power Dissipation



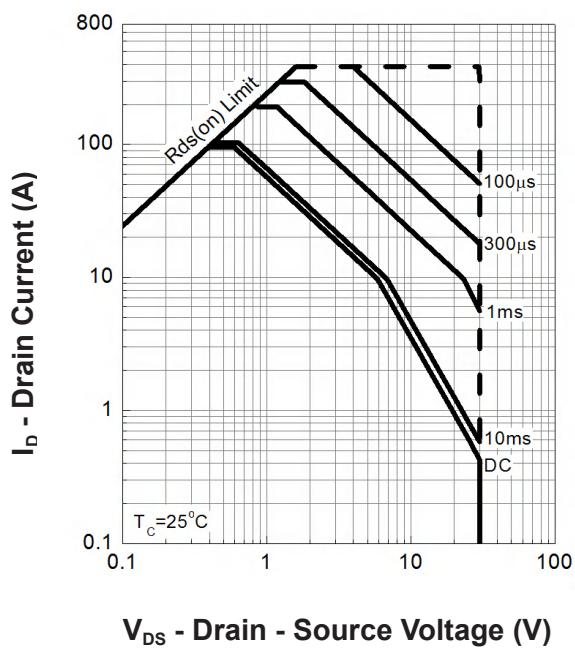
Drain Current



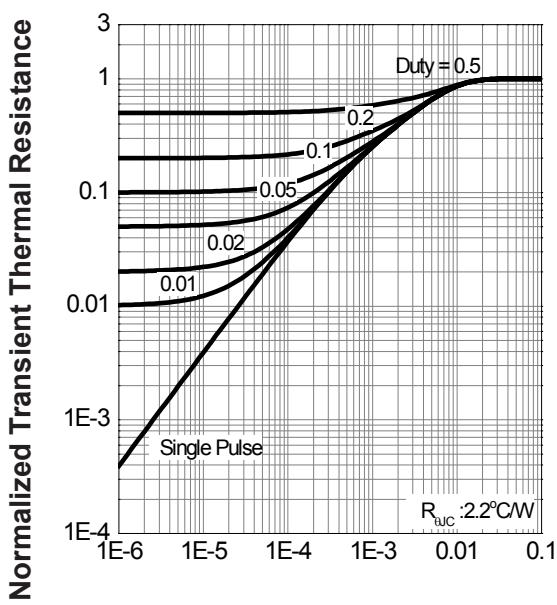
T_j - Junction Temperature ($^{\circ}\text{C}$)

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Safe Operation Area



Thermal Transient Impedance

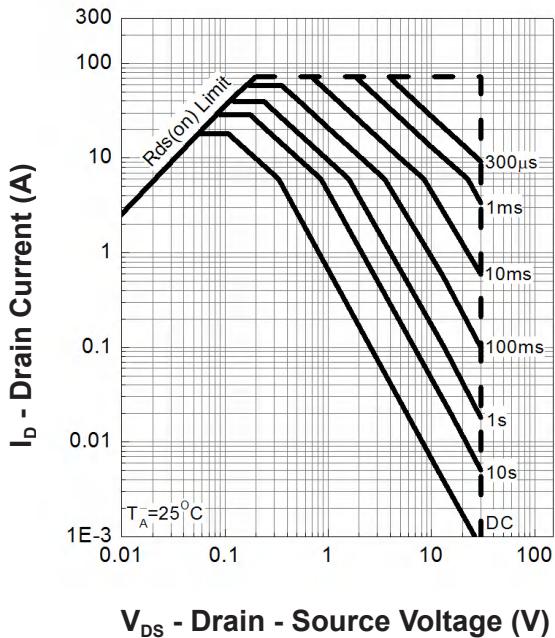


$\text{Square Wave Pulse Duration (sec)}$

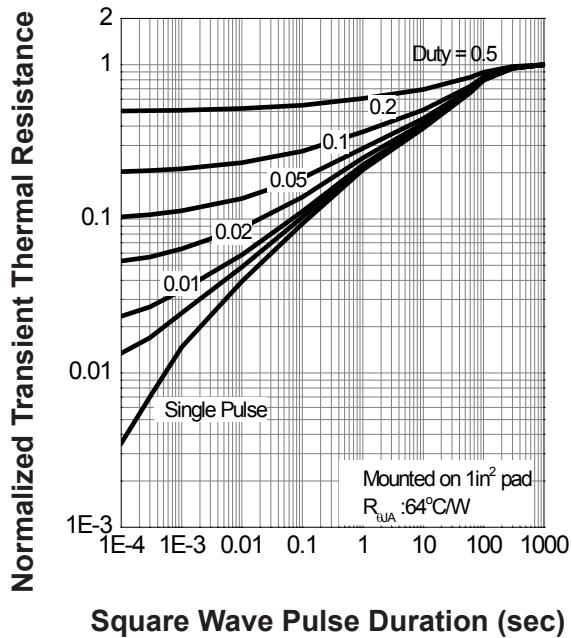


Typical Operating Characteristics(Cont.)

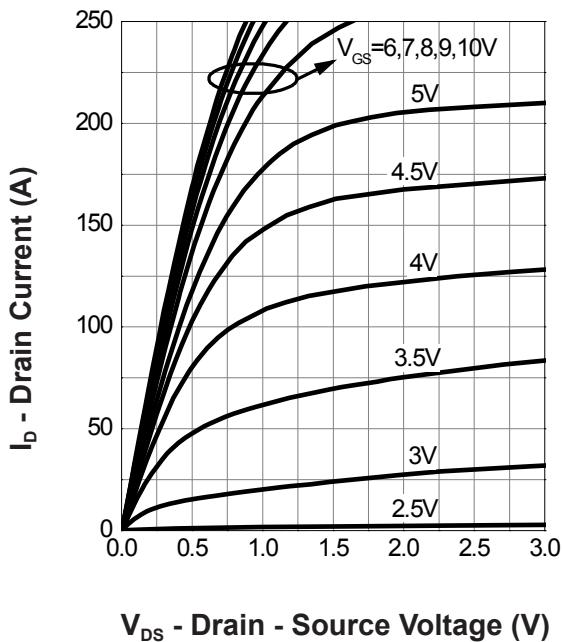
Safe Operation Area



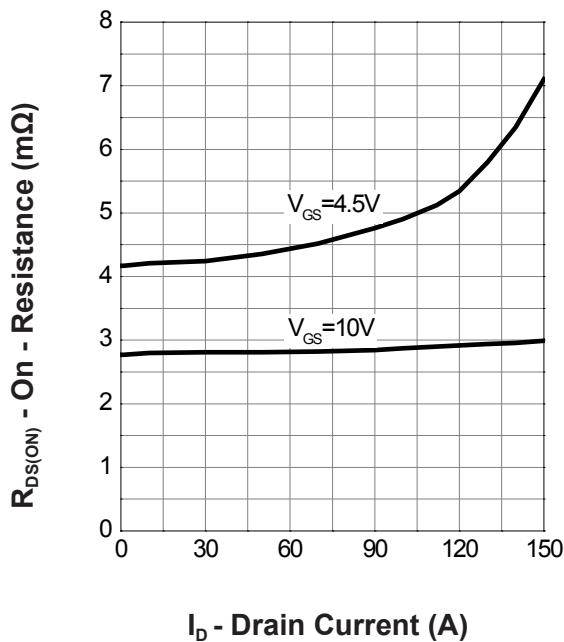
Thermal Transient Impedance



Output Characteristics



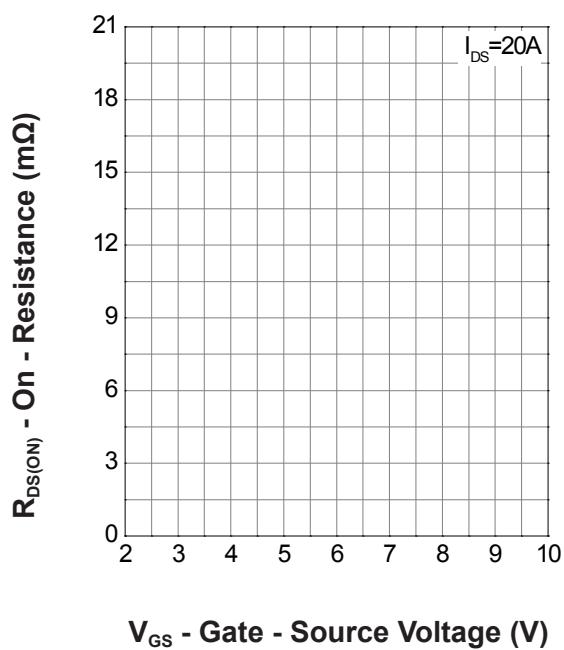
Drain-Source On Resistance



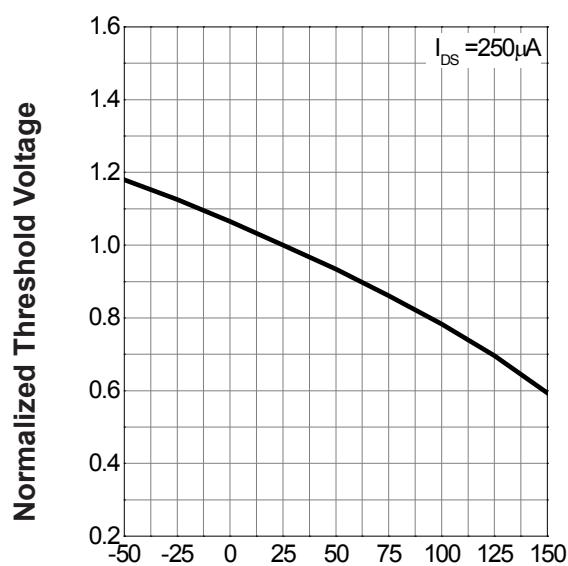


Typical Operating Characteristics(Cont.)

Gate-Source On Resistance



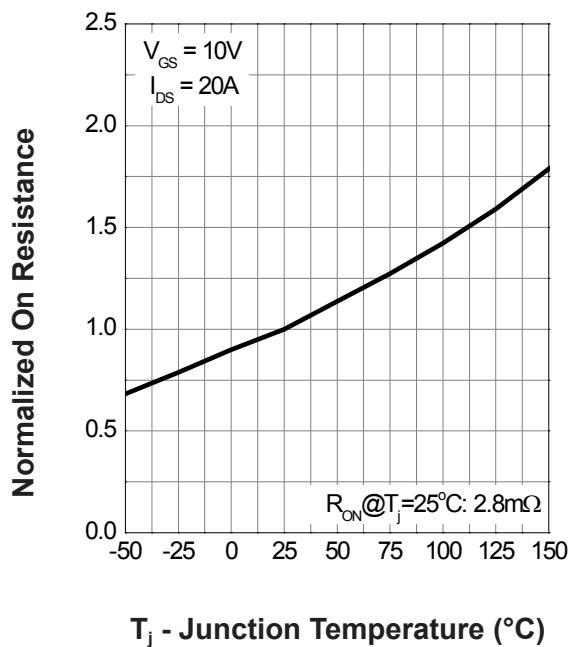
Gate Threshold Voltage



V_{GS} - Gate - Source Voltage (V)

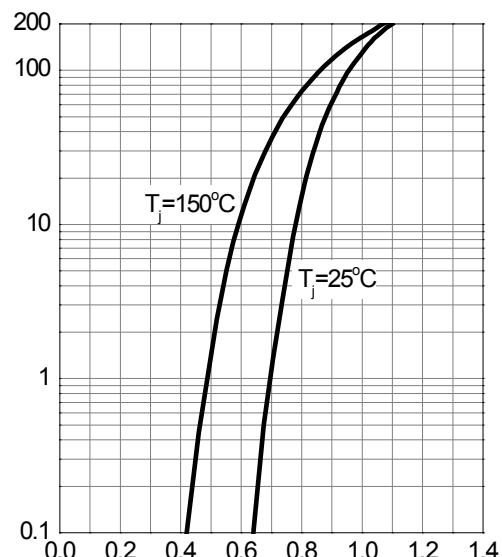
T_j - Junction Temperature (°C)

Drain-Source On Resistance



T_j - Junction Temperature (°C)

Source-Drain Diode Forward

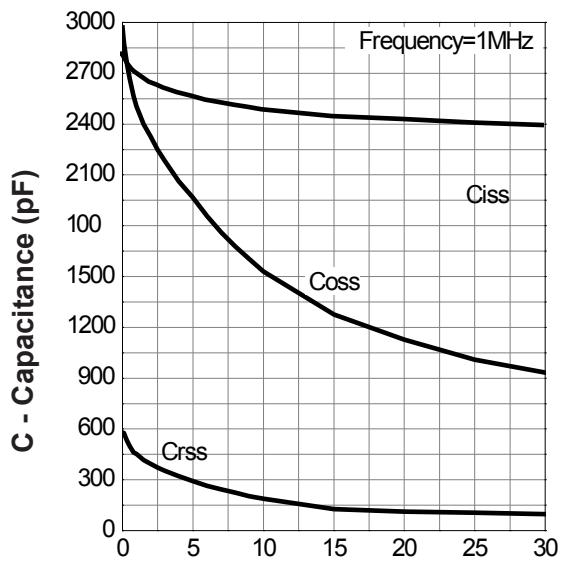


V_{SD} - Source - Drain Voltage (V)

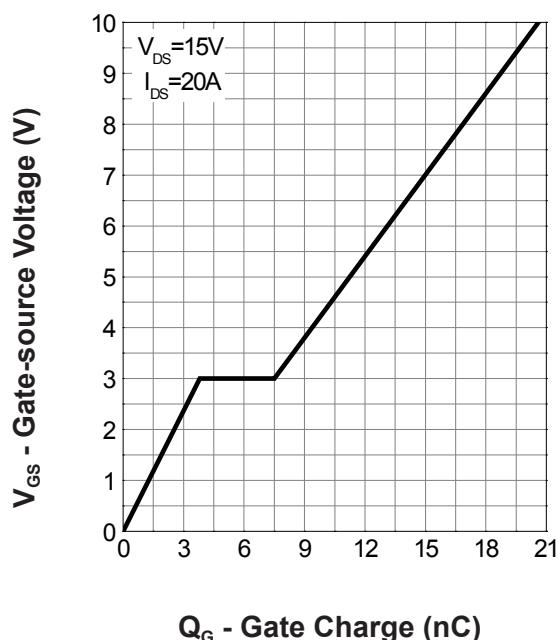


Typical Operating Characteristics(Cont.)

Capacitance



Gate Charge

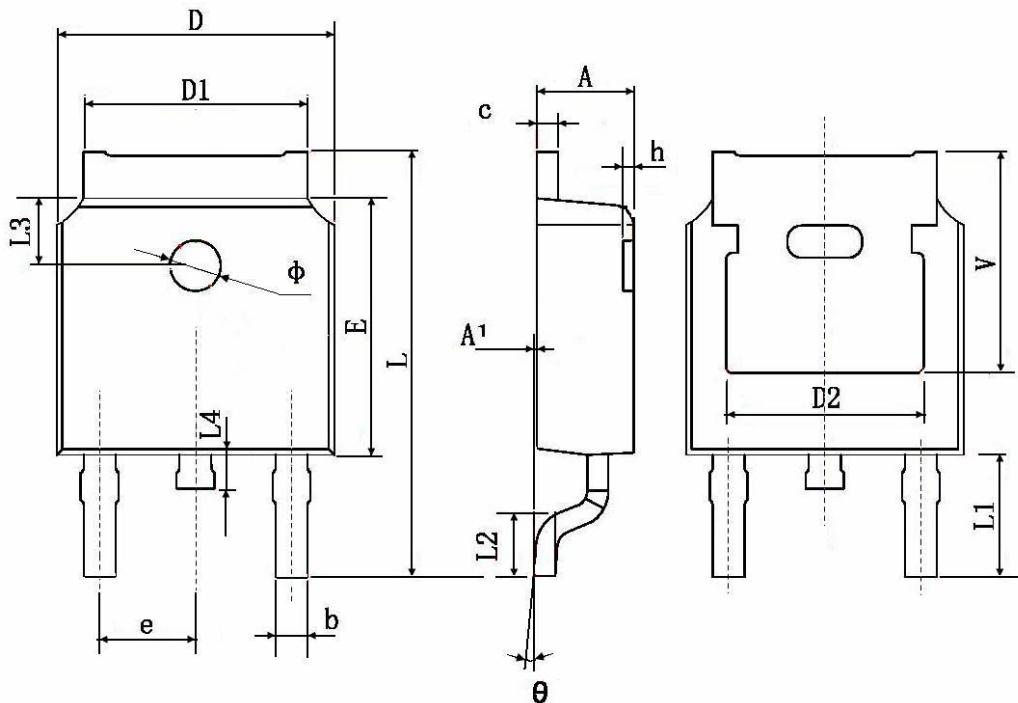


V_{DS} - Drain-Source Voltage (V)

Q_G - Gate Charge (nC)



TO252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	0.483 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	



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